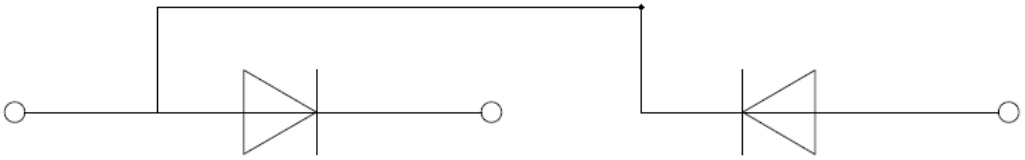
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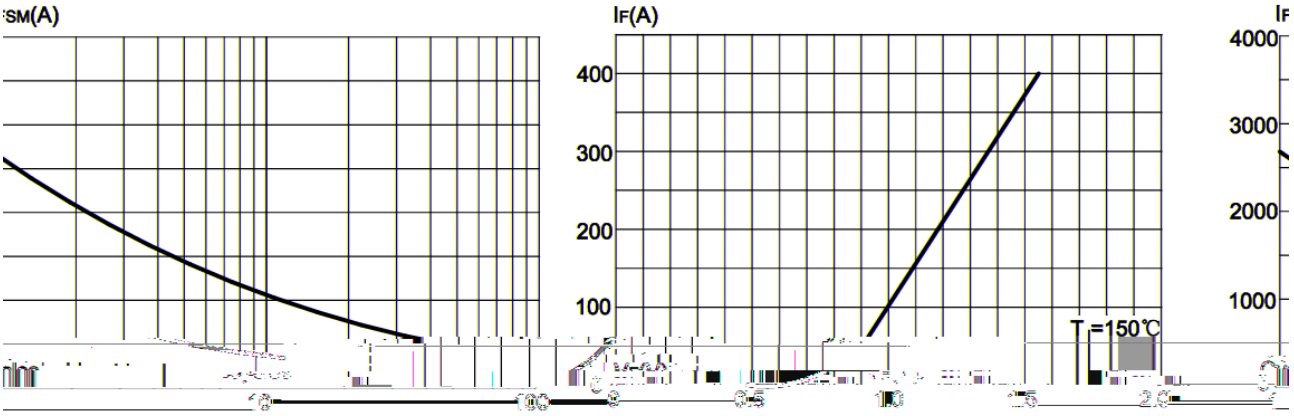


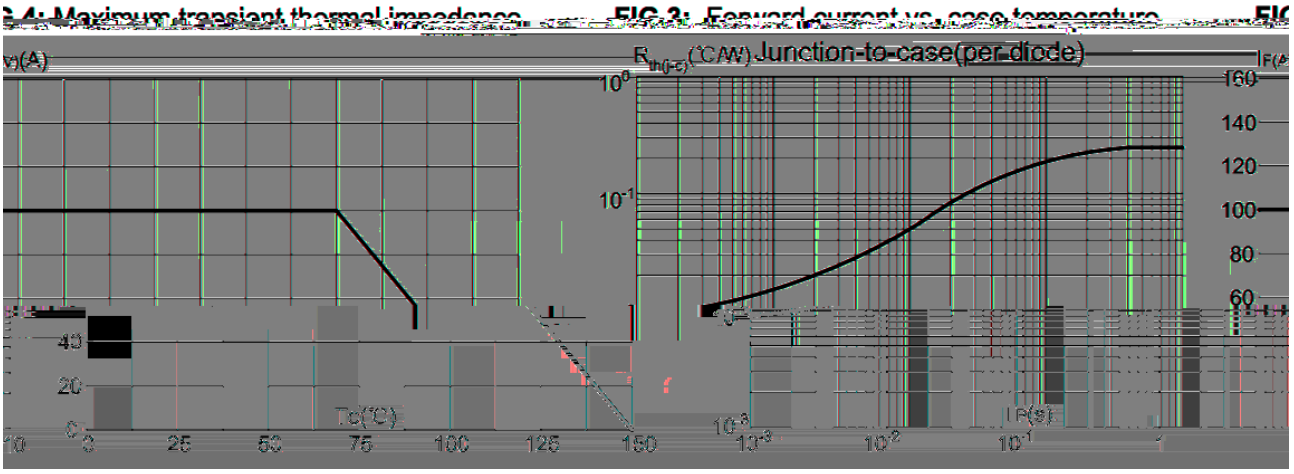


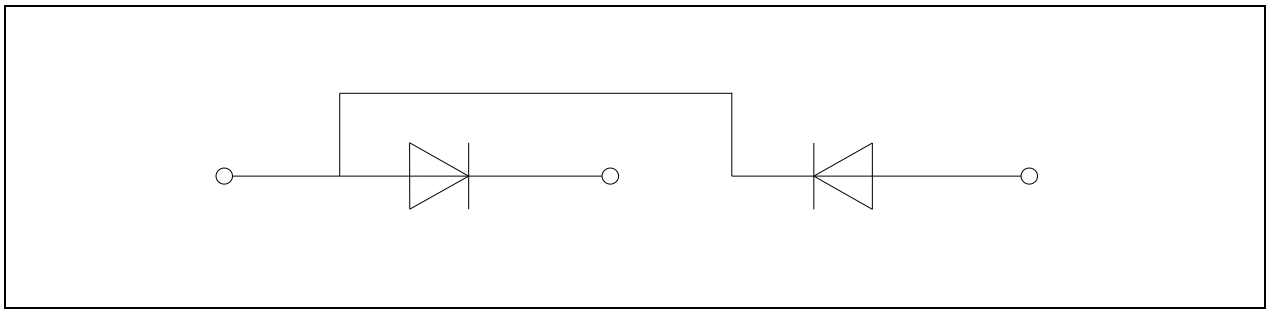
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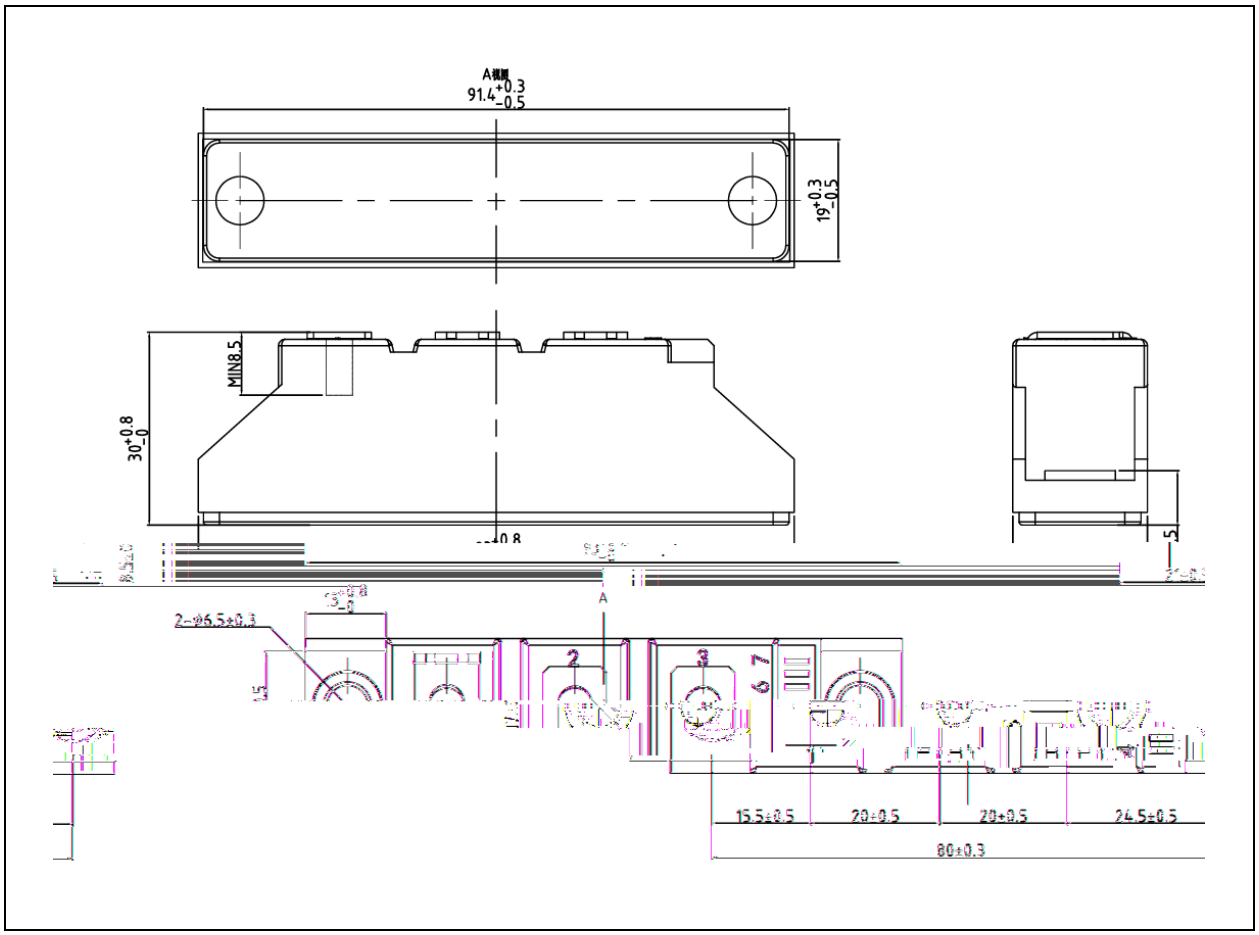
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IF(A)
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200
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4000
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Junction-to-case(per diode)
10^{0}
10^{-1}
160
140
120
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80
60
40
20
0
Tc(℃)
0
25
50
75
100
125
150
10^{-3}
10^{-2}
10^{-1}




91.4+0.3 -0.5
19+0.3 -0.5
MIN8.5
30+0.8 -0
2-φ6.5±0.3
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